

PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	40	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MMPQ2907	
PD	Total Device Dissipation Derate above 25°C	1,000 8.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient Effective 4 Die Each Die	125 240	°C/W °C/W °C/W

*Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

**Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

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(continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHAI	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0$	40		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	5.0		V
EBO	Emitter Cutoff Current	V _{EB} = 30 V		50	nA
СВО	Collector Cutoff Current	V _{CB} = 30 V		50	nA
	Collector-Emitter Saturation	$I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}^{*}$ $I_{C} = 300 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 500 \text{ mA}, V_{CE} = 10 \text{ V}^{*}$ $I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}$	100 30 50	0.4	V
IFE	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 150 \text{ mA}, V_{CE} = 10 \text{ V}^{*}$	75 100	300	
1	Collector Emitter Saturation	I _C = 500 mA, V _{CE} = 10 V*		0.4	V
V _{CE(sat)}	Voltage*	$I_{\rm C} = 300 \text{ mA}, I_{\rm B} = 30 \text{ mA}$		1.6	v
	Base-Emitter Saturation Voltage width ≤ 300 µs, Duty Cycle ≤ 2.0%	$I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}^{*}$ $I_{C} = 300 \text{ mA}, I_{B} = 30 \text{ mA}$		1.3 2.6	V V
ulse Test: Pulse	e Width ≤ 300 μs, Duty Cycle ≤ 2.0%	$I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}^{*}$ $I_{C} = 300 \text{ mA}, I_{B} = 30 \text{ mA}$	Emitter S	1.3 2.6	<u>v</u>
Туріса	9 Width ≤ 300 μs, Duty Cycle ≤2.0%	$I_{C} = 150 \text{ mA}, I_{B} = 15 \text{ mA}^{*}$		1.3 2.6	V

Spice Model

PNP (Is=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 Ise=54.81f Ikf=1.079 Xtb=1.5 Br=3.563 Nc=2 Isc=0 Ikr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cje=19.82p Mje=.3357 Vje=.75 Tr=111.3n Tf=603.7p Itf=.65 Vtf=5 Xtf=1.7 Rb=10)

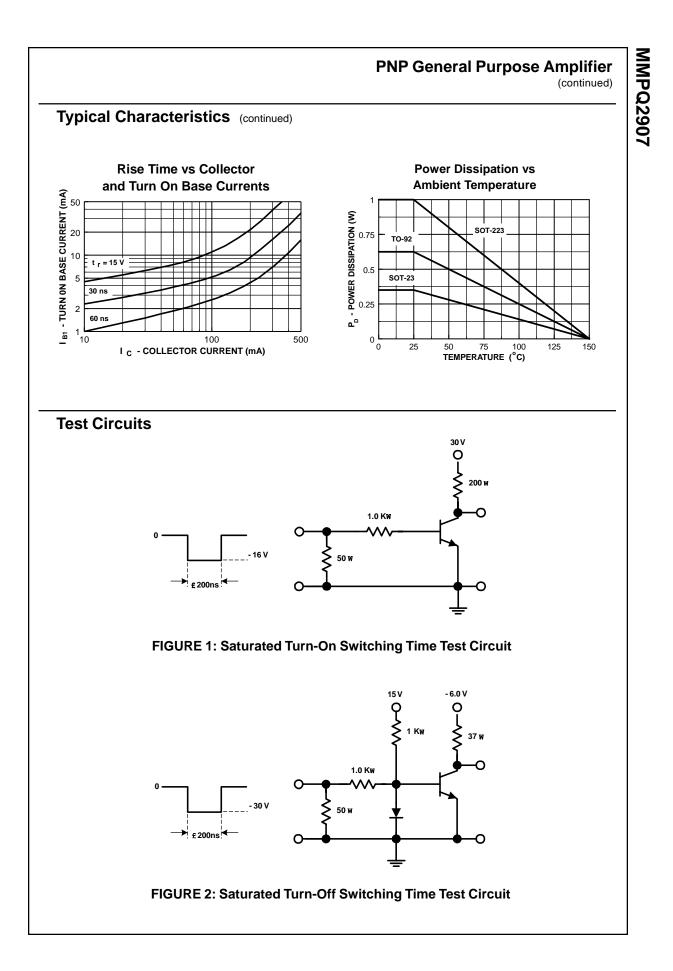
MMPQ2907

MMPQ2907

(continued)

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Typical Characteristics (continued) **Base-Emitter Saturation** Base Emitter ON Voltage vs **Voltage vs Collector Current Collector Current** 1 0.6 0.0 1 0.6 0.0 1 0.6 0.4 0.4 0.4 40 °C 40 °C = 25 25 125 °C ß 10 _ $V_{CE} = 5V$ V_{BESAT}- I 0 0 0.1 10 100 500 25 1 1 10 I c- COLLECTOR CURRENT (mA) I c - COLLECTOR CURRENT (mA) **Collector-Cutoff Current** Input and Output Capacitance vs. Ambient Temperature vs Reverse Bias Voltage I₀₈₀- COLLECTOR CURRENT (nA) 20 V_{CB}= 35V **CAPACITANCE (pF)** 8 7 7 7 с_{іb} 0 ∟ −0.1 100 125 50 75 -1 -10 - 50 T_A- AMBIENT TEMPERATURE (°C) **REVERSE BIAS VOLTAGE (V) Switching Times Turn On and Turn Off Times** vs Collector Current vs Collector Current 250 500 = |_{B2}= I_{B1} B2 10 10 200 400 15 \ - 15 \ **Su** 150 **S** 300 **BU** 100 **BMI** 200 off 50 100 0 L 10 on 0 L 10 100 I _C - COLLECTOR CURRENT (mA) 100 I _C - COLLECTOR CURRENT (mA) 1000 1000



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